Docket No.: MIT9944

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT:	McGill et al.	**GROUP:**	**Unknown**
SERIAL NO:	Unknown	**EXAMINER:**	Unknown
FILED:	Herewith		

FOR: YELLOW-GREEN EPITAXIAL TRANSPARENT SUBSTRATE-LEDS AND LASERS BASED ON A STRAINED-INGAP QUANTUM WELL GROWN ON AN INDIRECT BANDGAP SUBSTRATE

Mail Stop Patent Application
Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

In compliance with 37 C.F.R. §§1.56, 1.97, and 1.98, Applicant submits copies of the documents listed on the attached Form PTO-1449.

The Commissioner is authorized to charge Deposit Order Account No. 19-0079 for any further fee that may be required.

Respectfully submitted,

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I hereby certify that this Information Disclosure Statement and the documents referred to as enclosed therein are being deposited with the United States Postal Service on **August 1, 2003** in an envelope as "Express Mail Post Office to Addressee" Mailing Label Number **EV303918033US** addressed to the: Mail Stop Patent Application, P.O. Box 1450, Commissioner of Patents, Alexandria, VA 22313-1450.

Emily C. Porell

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08/01/2003

Date

FORM PTO-1449 (Rev. 5/92)	SAMUELS, GAUTHIER & STEVENS LLP 225 Franklin Street, Boston, MA 02110 Telephone: (617) 426-9180	MIT.9944 ATTORNEY DOCKET NO.	Unknown SERIAL NO.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT: McGill et al. FILING DATE: Herewith	GROUP: Unknown EXAMINER: Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	6,064,076	05/16/2000	Chen et al.			05/20/1998
	AB	5,751,753	05/12/1998	Uchida			07/23/1996
	AC	6,433,364	08/13/2002	Hosoba et al.			03/29/2001
	AD	6,081,540	06/27/2000	Nakatsu			12/18/1997
	AE	5,300,794	04/05/1994	Melman et al			03/19/1991
	AF	5,363,392	11/08/1994	Kasukawa et al.			11/18/1992
	AG						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AH						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AI	"Growth and Characterization of InGaP Yellow-Green Light-Emitting Diodes by Liquid-Phase Epitaxy," Chen et al. *Japanese Journal of Applied Physics*. January 1992. Vol. 31.
	AJ	"High-Efficiency InGaP Light-Emitting Diodes on GaP Substrates," Stinson et al. *Applied Physics Letters*. May 1991. Vol. 58, No. 18.
	AK	"AlGaInP/GaInP Double-Heterostructure Orange Light-Emitting Diodes on GaAsP Substrates Prepared by Metalorganic Vapor-Phase Epitaxy," Lin et al. *Journal of Crystal Growth*. 1994. Vol. 137.
	AL	"Metalorganic Vapor Phase EpitaxyGrowth and Characterization of $(Al_xGa_{1-x})_{0.5}In_{0.5}P/Ga_{0.5}\ In_{0.5}P$ (x=0.4, 0.7, and 1.0) Quantum Wells on 15°-Off-(100) GaAs Substrates at High Growth Rate," Jou et al. *Japanese Journal of Applied Physics*. October 1993. Vol. 32, No. 10.
	AM	"Yellow-Green Emission for ETS-LEDs and lasers based on a strained-InGaP quantum well heterostructure grown on a transparent, compositionally graded AlInGaP buffer," McGill et al. *Mat. Res. Symp. Proc.* 2003. Vol. 744
	AN	"Growth and Characterization of Lattice-Mismatched $In_xGa_{1-x}P$ Yellow Light Emitting Diodes on GaP," Paul Liu, Phd. Thesis. University of Illinois. 1997.

EXAMINER	DATE CONSIDERED

EXAMINER: **Initial if citati n c nsidered, wh ther r n t citati n is in c nf rmance with MPEP 609; draw line thr ugh citation if n t in c nf rmance and n t c nsidered. Include c py f this f rm with next c mmunication to applicant.**